

## SnCl<sub>2</sub> を添加した鉛フリーハライドペロブスカイト薄膜

### および太陽電池の特性

#### Role of SnCl<sub>2</sub> as additive on lead-free halide Perovskite thin films and solar cell devices

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Tin halide perovskite solar cells have been investigated as primary alternative for lead halide based solar cells to solve the environmental impact for toxicity of lead [1]. However, the instability of divalent tin (Sn<sup>2+</sup>) has been problematic, leading the low photovoltaic performance compared to methylammonium lead triiodide, MAPbI<sub>3</sub>, based solar cells. Usually, excess tin halide, mainly SnF<sub>2</sub>, has been used to overcome this instability issue since it has been proven to be effective for reducing tin vacancy upon fabrication [2]. Recent progress on tin halide perovskite solar cells demonstrated that the combination of excess tin (Sn<sup>2+</sup>) and reducing conditions is the key for making tin halide based devices workable [3]. Besides SnF<sub>2</sub>, SnCl<sub>2</sub> could be a potential additive since it meets the prerequisite, excess Sn<sup>2+</sup> and reducing conditions. Additionally, inclusion of chloride have been reported to be uniquely beneficial for improvements in crystal growth and optical properties [4]. To date, however, only limited work has been reported to address the effectiveness of SnCl<sub>2</sub> as additive [5]. Therefore it is important to achieve extended study on the role of SnCl<sub>2</sub> for tin halide perovskites in order to obtain further insight into advantages and obstacles on the lead-free device performance and their optoelectronic properties.

We studied the phase characterization using X-ray powder diffraction, film morphology with scanning electron microscopy, and carrier lifetimes with optical measurements, together with device fabrication. The devices were fabricated using one step method with/without antisolvent dripping step, which turned to be partly influential for device performance. We will present further studies on improvement in the device performance and optical properties.

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